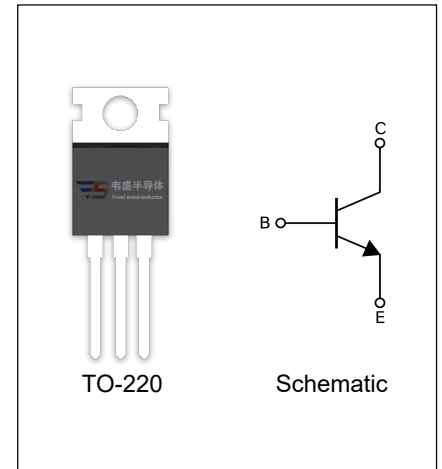


13003 TRANSISTOR (NPN)

FEATURES

- power switching applications



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	T		Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =5mA, I _E =0	700			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =2mA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =700V, I _E =0			1	mA
Collector cut-off current	I _{CEO}	V _{CE} =400V, I _B =0			0.5	mA
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			1	mA
DC current gain	h _{FE1}	V _{CE} =5V, I _C = 0.5 A	20		40	
	h _{FE2}	V _{CE} =5V, I _C = 1.5A	5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =0.25A			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =1A, I _B =0.25A			1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C =100mA, f =1MHz	5			MHz
Fall time	t _f	I _C =1A, I _{B1} =-I _{B2} =0.2A, V _{CC} =100V			0.5	μs
Storage time	t _S	I _C =250mA (UI9600)	2		4	μ s

CLASSIFICATION OF h_{FE(1)}

Range	20-30	30-40
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CLASSIFICATION OF t_S

Rank	A	B
Range	2.0-3.0 (μ s)	3.0-4.0(μ s)